

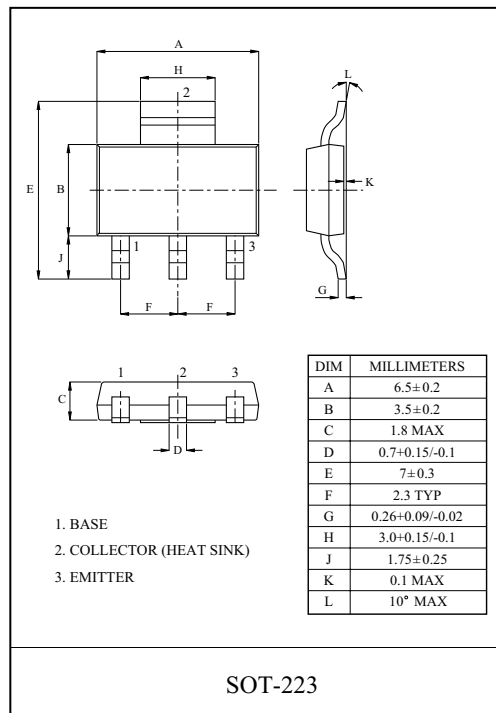
HIGH VOLTAGE APPLICATION.
TELEPHONE APPLICATION.

FEATURES

- High Breakdown Voltage.
- Collector Power Dissipation : $P_C=2W(T_C=25^\circ C)$

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	500	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	300	mA
Collector Power Dissipation ($T_C=25^\circ C$)	P_C	2	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C

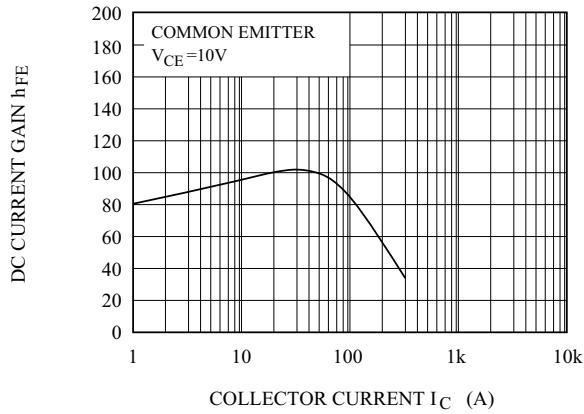


ELECTRICAL CHARACTERISTICS (Ta=25°C)

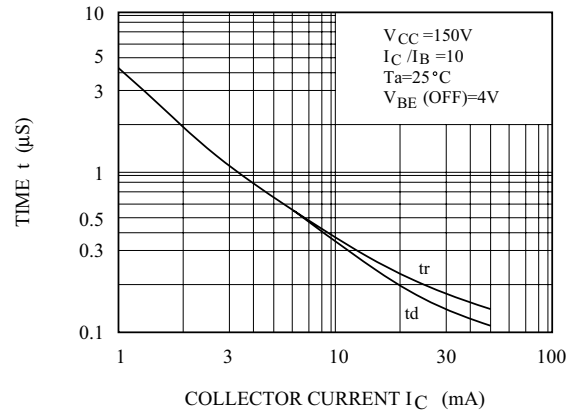
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	500	-	-	V
Collector-Emitter Breakdown Voltage (1)	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	400	-	-	V
Collector-Emitter Breakdown Voltage (2)	$V_{(BR)CES}$	$I_C=100\mu A, I_B=0$	400	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6.0	-	-	V
Collector Cut off Current	I_{CBO}	$V_{CB}=400V, I_E=0$	-	-	100	nA
		$V_{CB}=320V, I_E=0$	-	-	-	-
Collector Cut off Current	I_{CES}	$V_{CE}=400V, I_B=0$	-	-	500	nA
		$V_{CE}=320V, I_B=0$	-	-	-	-
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$	-	-	100	nA
DC Current Gain *	h_{FE}	$V_{CE}=10V, I_C=1mA$	40	-	-	
		$V_{CE}=10V, I_C=10mA$	50	-	200	
		$V_{CE}=10V, I_C=50mA$	45	-	-	
		$V_{CE}=10V, I_C=100mA$	40	-	-	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	0.5	V
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	0.75	V
Collector Output Capacitance	C_{ob}	$V_{CB}=20V, I_E=0, f=1MHz$	-	-	7	pF

*Pulse Test : Pulse Width $\leq 300\mu S$, Duty Cycle $\leq 2.0\%$

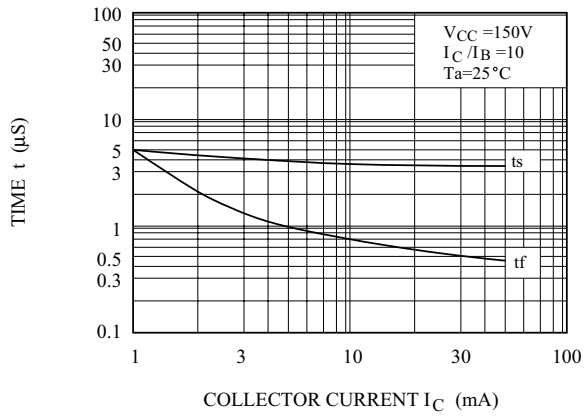
$h_{FE} - I_C$



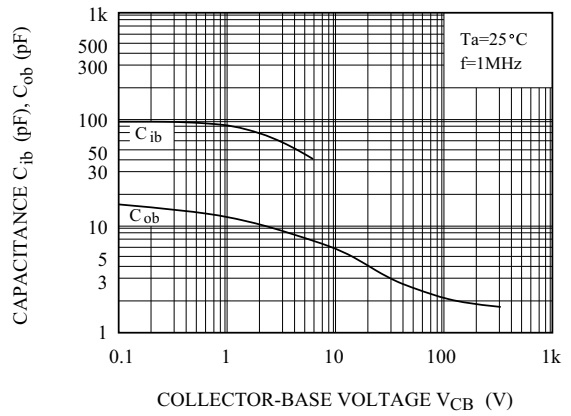
TURN-ON SWITCHING CHARACTERISTICS



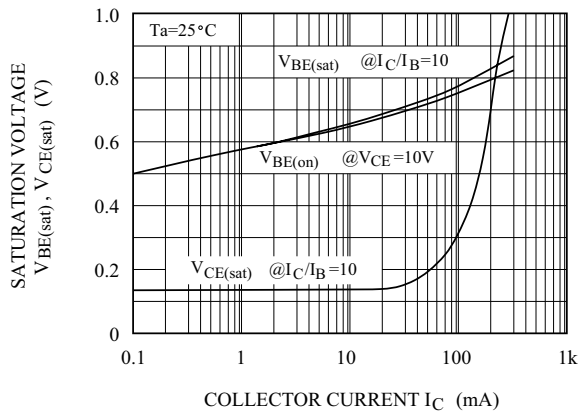
TURN-OFF SWITCHING CHARACTERISTICS



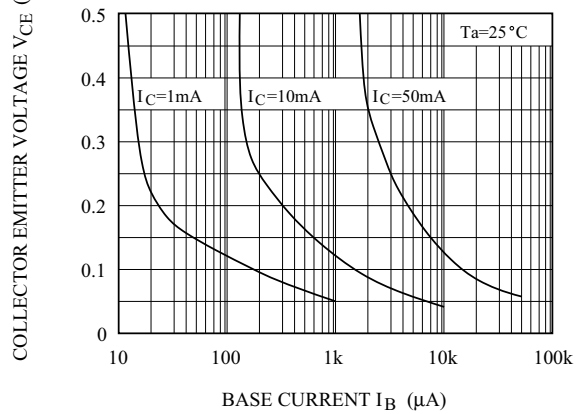
$C_{ib}, C_{ob} - V_{CB}$



$V_{BE(sat)}, V_{CE(sat)} - I_C$



COLLECTOR SATURATION REGION



PZTA44

